

**REMARKS:**

The present Amendment revises the specification, drawings and claims to conform to United States patent practice, before examination of the present PCT application in the United States National Examination Phase. All of the changes are editorial and no new matter is added thereby. Claims 1-15 have been canceled. New claims 16-30 are patentably distinguishable from the known prior art.

Early examination on the merits is respectfully requested.

Respectfully submitted,

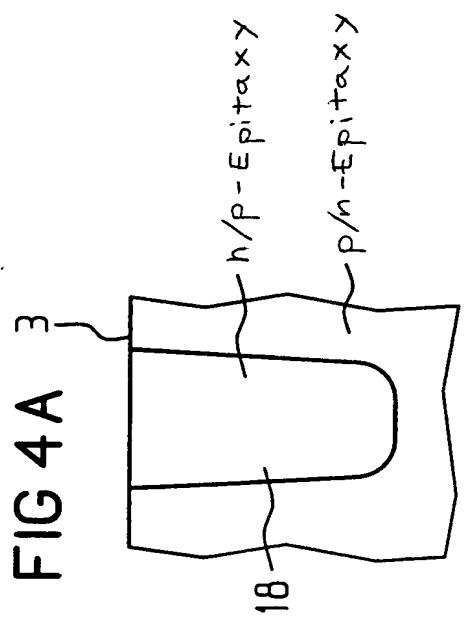
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(Reg. No. 31,870)

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**FIG 4B**

This diagram shows a similar cross-section to FIG 4A, but with a different doping profile. The substrate is labeled 'Undoped/lightly doped substrate'. The n/p-Epitaxy layer is labeled 'n/p-Diffusion'. The p/n-Epitaxy layer is labeled 'p/n-Diffusion'. A U-shaped recess is etched into the p/n-Epitaxy layer, exposing the n/p-Epitaxy layer underneath. The number '18' is written below the substrate.

**FIG 4C**

This diagram shows a cross-section of a semiconductor structure. The substrate is labeled 'Undoped/lightly doped substrate' at the bottom. The n/p-Epitaxy layer is labeled 'n/p-Diffusion'. The p/n-Epitaxy layer is labeled 'p/n-Diffusion'. A U-shaped recess is etched into the p/n-Epitaxy layer, exposing the n/p-Epitaxy layer underneath. The number '18' is written below the substrate.

**FIG 4D**

This diagram shows a cross-section of a semiconductor structure. The substrate is labeled 'Undoped/lightly doped substrate' at the bottom. The n/p-Epitaxy layer is labeled 'n/p-Diffusion'. The p/n-Epitaxy layer is labeled 'p/n-Diffusion'. A rectangular recess is etched into the p/n-Epitaxy layer, exposing the n/p-Epitaxy layer underneath. The numbers '21' and '23' are written below the substrate.